

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions, and listings, of claims in the application.**

**Listing of claims:**

1. (Currently Amended) A thin film transistor, comprising:

a stepped substrate provided with a sidewall between upper and lower portions thereof;

an active layer formed on the stepped substrate;

a gate insulation film formed on a lower portion of the active layer and a sidewall portion of the active layer contiguous the lower portion of the active layer and the sidewall of the stepped substrate, respectively;

an insulating film formed on a lower portion of the gate insulation film and a sidewall portion of the gate insulating film contiguous the lower portion of the gate insulating film and the sidewall portion of the ~~stepped substrate~~ active layers, respectively;

a gate electrode formed on the gate insulation film corresponding to an upper part of the sidewalls of the substrate and the insulation film;

impurity regions in the active layer corresponding to the upper and lower portions of the substrate; and

an offset region formed ~~on the whole~~ a lower region of the sidewall and substrate corresponding to the insulating film as a single region sidewall portion of the active layer and the lower portion of the active layer below a bottom of the insulating layer.

2. (Original) The thin film transistor of claim 1, wherein the stepped substrate is formed on an insulating material.

3. (CANCELLED)

4. (Original) The thin film transistor of claim 1, wherein the active layer is a semiconductor film.

5. (Currently Amended) The thin film transistor of claim 1, wherein the insulation film is formed of a spin-on-glass ~~film~~.

6. (Currently Amended) The thin film transistor of claim 1, wherein a portion of the active layer corresponding to the gate electrode is a channel region, and a portion thereof corresponding to the ~~insulation~~ insulating film is an offset region.

CLAIMS 7-14 (CANCELLED)